



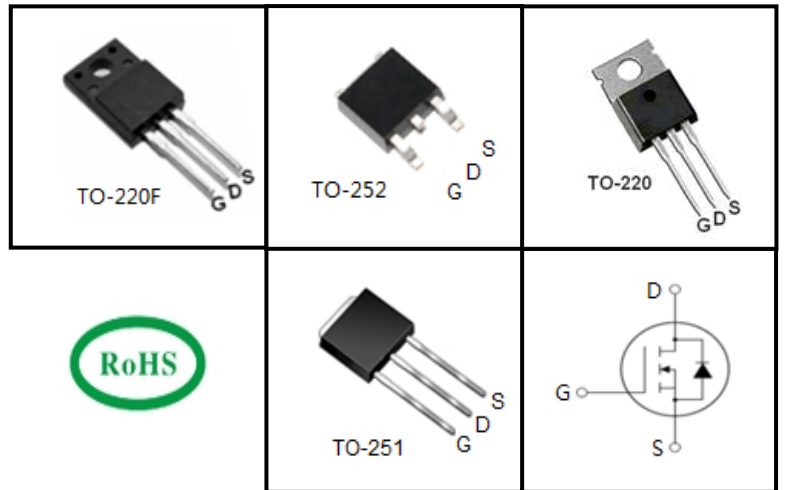
## 900V N-Channel MOSFET

### FEATURES

- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

### APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)



Device Marking and Package Information				
Device	TMA2N90HG	TMD2N90HG	TMP2N90HG	TMU2N90HG
Package	TO-220F	TO-252	TO-220	TO-251
Marking	A2N90HG	D2N90HG	P2N90HG	U2N90HG

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Value				Unit
		TO-220F	TO-252	TO-220	TO-251	
Drain-Source Voltage ( $V_{GS} = 0V$ )	$V_{DSS}$	900				V
Continuous Drain Current	$I_D$	2				A
Pulsed Drain Current (note1)	$I_{DM}$	8				A
Gate-Source Voltage	$V_{GSS}$	$\pm 30$				V
Single Pulse Avalanche Energy (note2)	$E_{AS}$	108				mJ
Avalanche Current (note1)	$I_{AR}$	2				A
Repetitive Avalanche Energy (note1)	$E_{AR}$	7.1				mJ
Power Dissipation ( $T_C = 25^\circ\text{C}$ )	PD	39	107			W
Reverse diode dv/dt, $V_{DS} = 0 \dots 480V$ , $I_{SD} \leq I_D$	dv/dt	4.5				V/ns
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55~+150				$^\circ\text{C}$

Thermal Resistance						
Parameter	Symbol	Value				Unit
		TO-220F	TO-252	TO-220	TO-251	
Thermal Resistance, Junction-to-Case	$R_{thJC}$	3.2	1.17			$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient	$R_{thJA}$	62.5	62.5			



Specifications $T_J = 25^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	900	--	--	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 900V, V_{GS} = 0V, T_J = 25^\circ\text{C}$	--	--	1	$\mu A$
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 30V$	--	--	$\pm 100$	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	3.0	--	4.0	V
Drain-Source On-Resistance (Note3)	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 1A$	--	5	6	$\Omega$
Forward Transconductance (Note3)	$g_{fs}$	$V_{DS} = 10V, I_D = 1A$	--	3	--	S
<b>Dynamic</b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0V,$ $V_{DS} = 25V,$ $f = 1.0\text{MHz}$	--	488	--	pF
Output Capacitance	$C_{oss}$		--	62	--	
Reverse Transfer Capacitance	$C_{rss}$		--	12	--	
Total Gate Charge	$Q_g$	$V_{DD} = 720V, I_D = 2A,$ $V_{GS} = 10V$	--	20	--	nC
Gate-Source Charge	$Q_{gs}$		--	2.2	--	
Gate-Drain Charge	$Q_{gd}$		--	11	--	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 400V, I_D = 2A,$ $R_G = 25\Omega$	--	31	--	ns
Turn-on Rise Time	$t_r$		--	61	--	
Turn-off Delay Time	$t_{d(off)}$		--	80	--	
Turn-off Fall Time	$t_f$		--	44	--	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Body Diode Current	$I_S$	$T_C = 25^\circ\text{C}$	--	--	2	A
Pulsed Diode Forward Current	$I_{SM}$		--	--	8	
Body Diode Voltage	$V_{SD}$	$T_J = 25^\circ\text{C}, I_{SD} = 2A, V_{GS} = 0V$	--	--	1.4	V
Reverse Recovery Time	$t_{rr}$	$V_R = 400V, I_F = I_S,$ $di_F/dt = 100A/\mu s$	--	629	--	ns
Reverse Recovery Charge	$Q_{rr}$		--	2.2	--	$\mu C$
Reverse Recovery Charge	$Q_{rr}$		--	7	--	$\mu C$

**Notes**

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2.  $I_{AS} = 2A, V_{DD} = 50V, R_G = 25\Omega, \text{Starting } T_J = 25^\circ\text{C}$
3. Pulse Test: Pulse width  $\leq 300\mu s, \text{Duty Cycle } \leq 1\%$



Typical Characteristics  $T_J = 25^\circ\text{C}$ , unless otherwise noted

Figure 1. Output Characteristics ( $T_J = 25^\circ\text{C}$ )

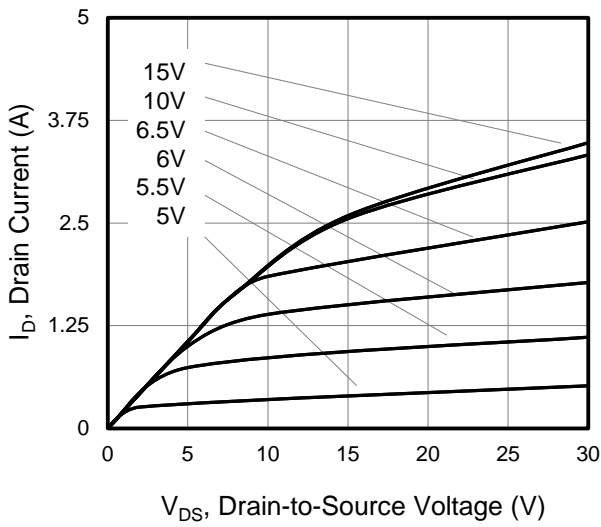


Figure 2. Transfer Characteristics

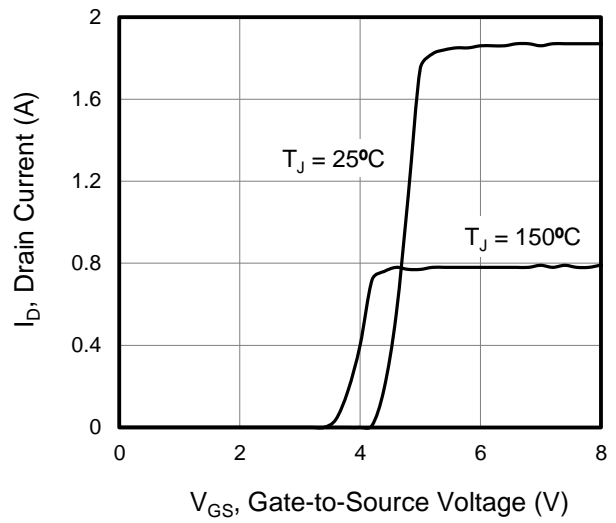


Figure 3. On-Resistance vs. Drain Current

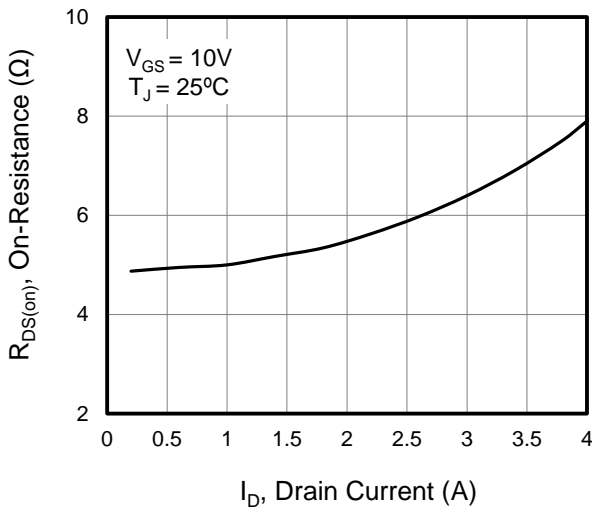


Figure 4. Capacitance

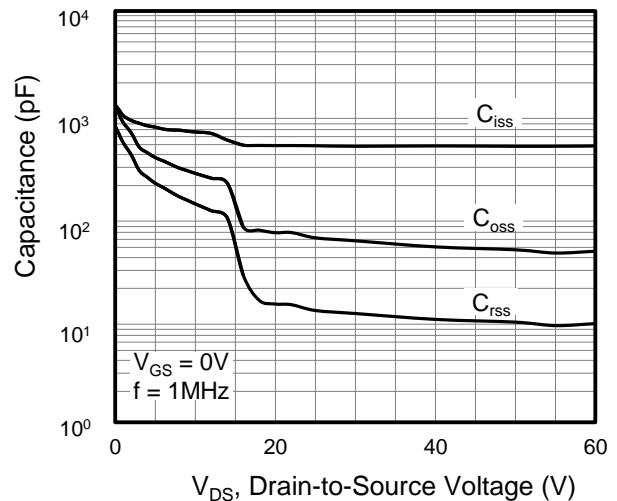


Figure 5. Gate Charge

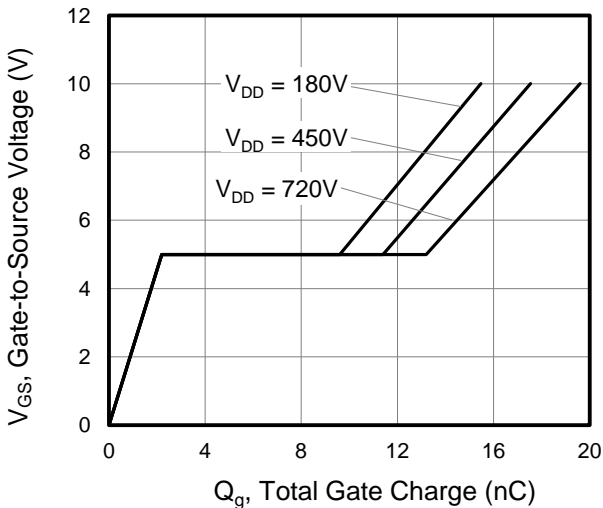
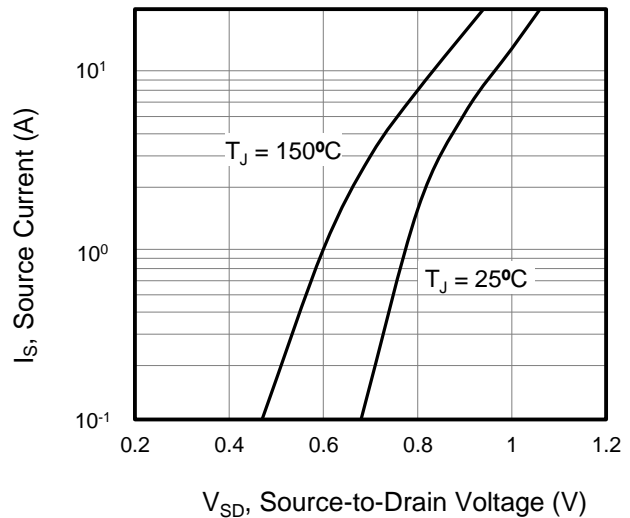


Figure 6. Body Diode Forward Voltage





Typical Characteristics  $T_J = 25^\circ\text{C}$ , unless otherwise noted

Figure 7. On-Resistance vs. Temperature

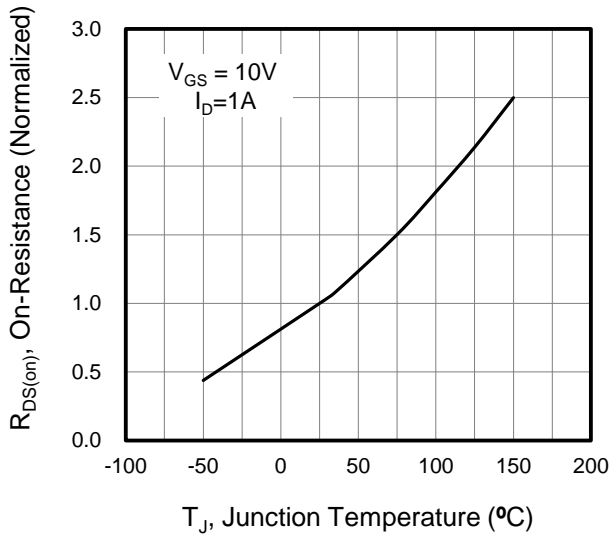


Figure 8. Breakdown voltage vs. Junction Temperature

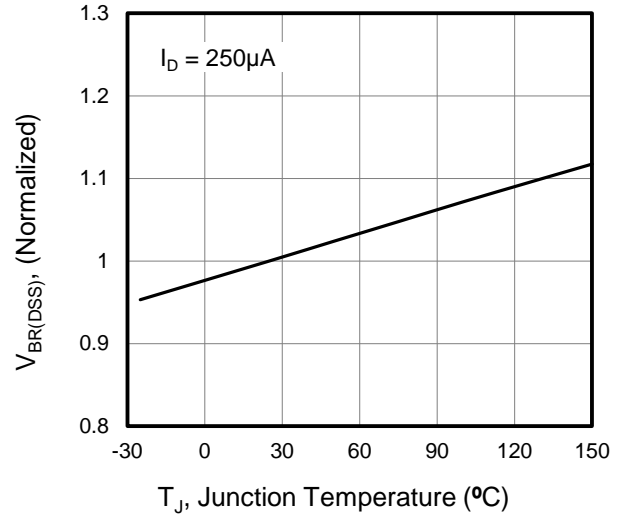


Figure 9. Transient Thermal Impedance

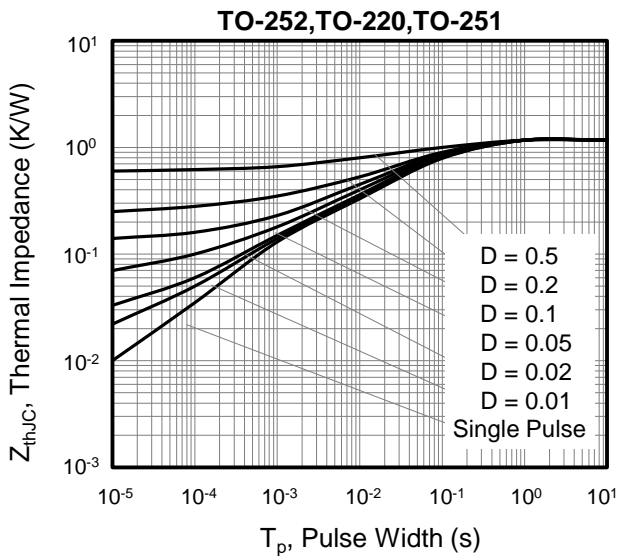


Figure 10. Transient Thermal Impedance

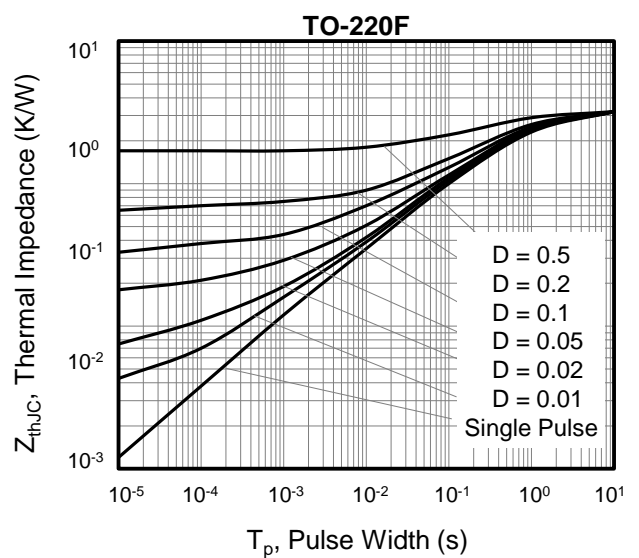


Figure 12. Safe operation area for

TO-252, TO-220, TO-251

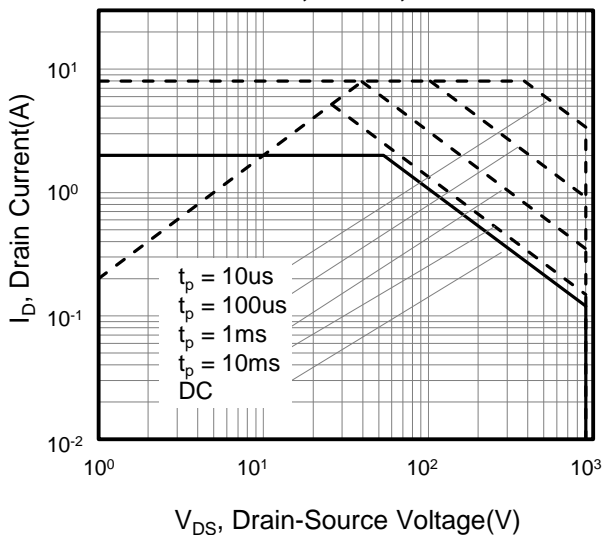


Figure 13. Safe operation area for

TO-220F

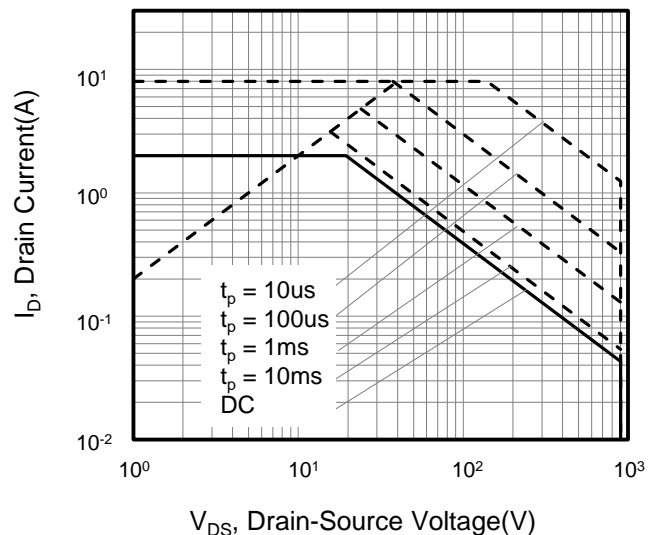




Figure A: Gate Charge Test Circuit and Waveform

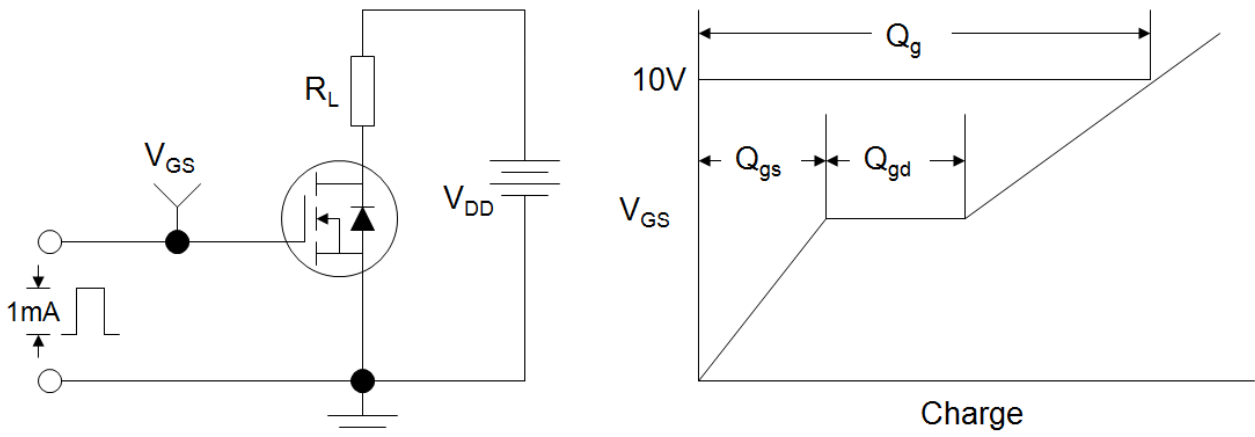


Figure B: Resistive Switching Test Circuit and Waveform

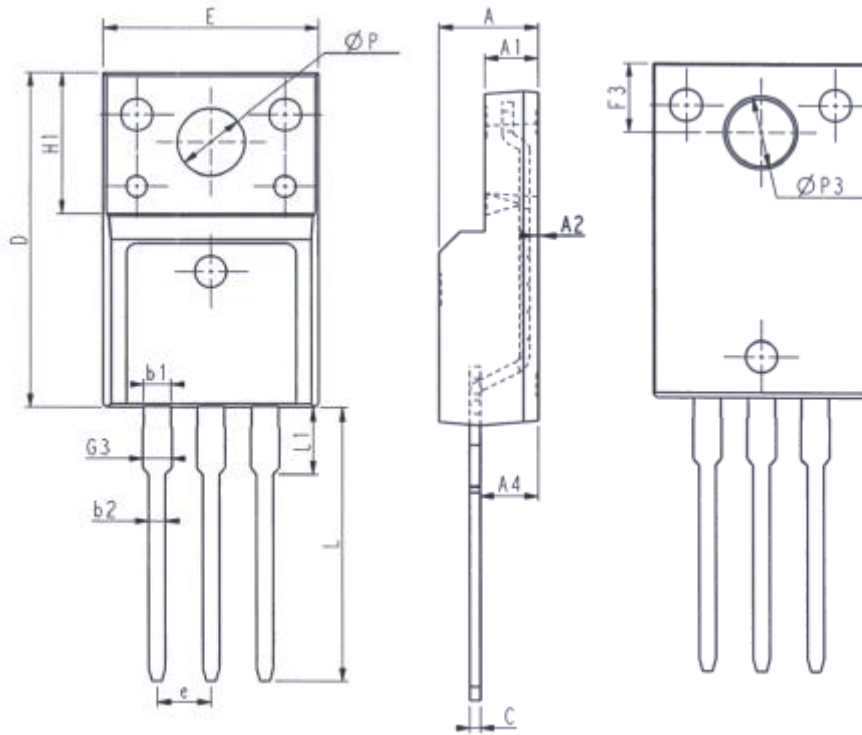


Figure C: Unclamped Inductive Switching Test Circuit and Waveform





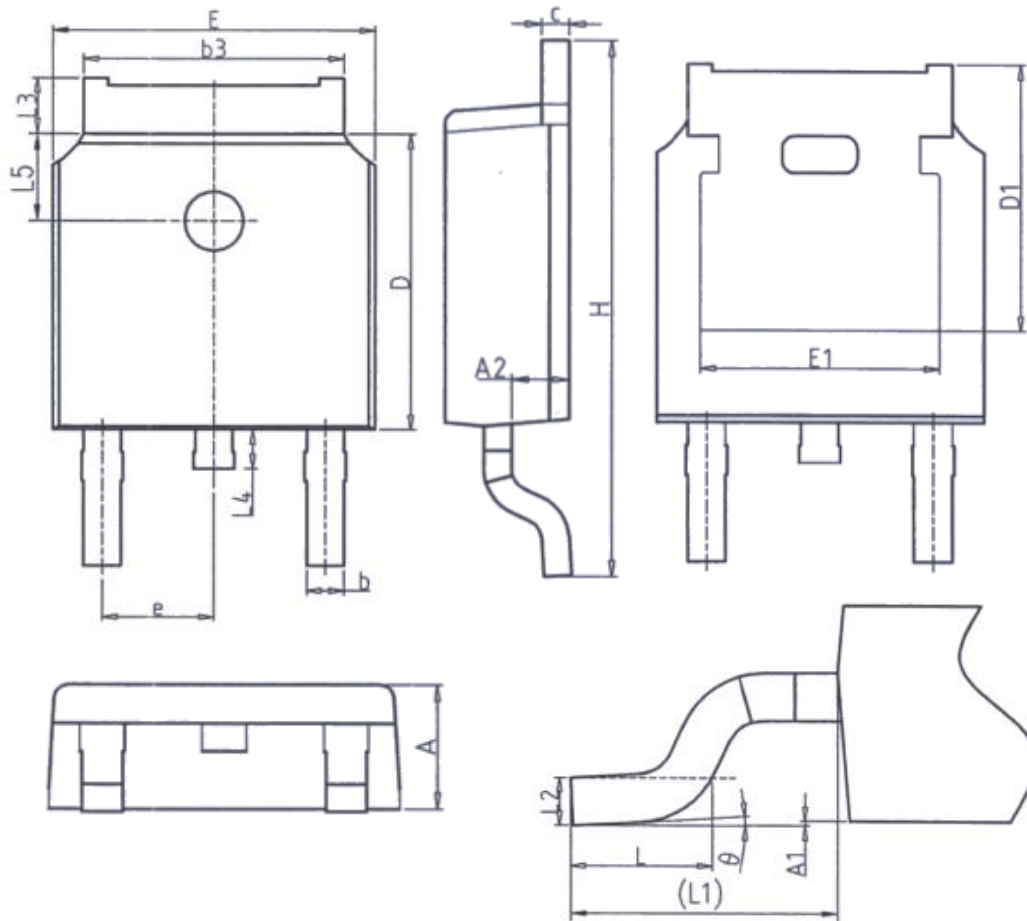
## TO-220F



Unit: mm			Unit: mm		
Symbol	Min.	Max.	Symbol	Min.	Max.
E	9.96	10.36	L	12.68	13.28
A	4.50	4.90	L1	2.93	3.13
A1	2.34	2.74	P	3.03	3.38
A2	0.30	0.60	P3	3.15	3.65
A4	2.56	2.96	F3	3.15	3.45
c	0.40	0.65	G3	1.25	1.55
D	15.57	16.17	b1	1.18	1.43
H1	6.70REF		b2	0.70	0.95
e	2.54BSC				



### TO-252

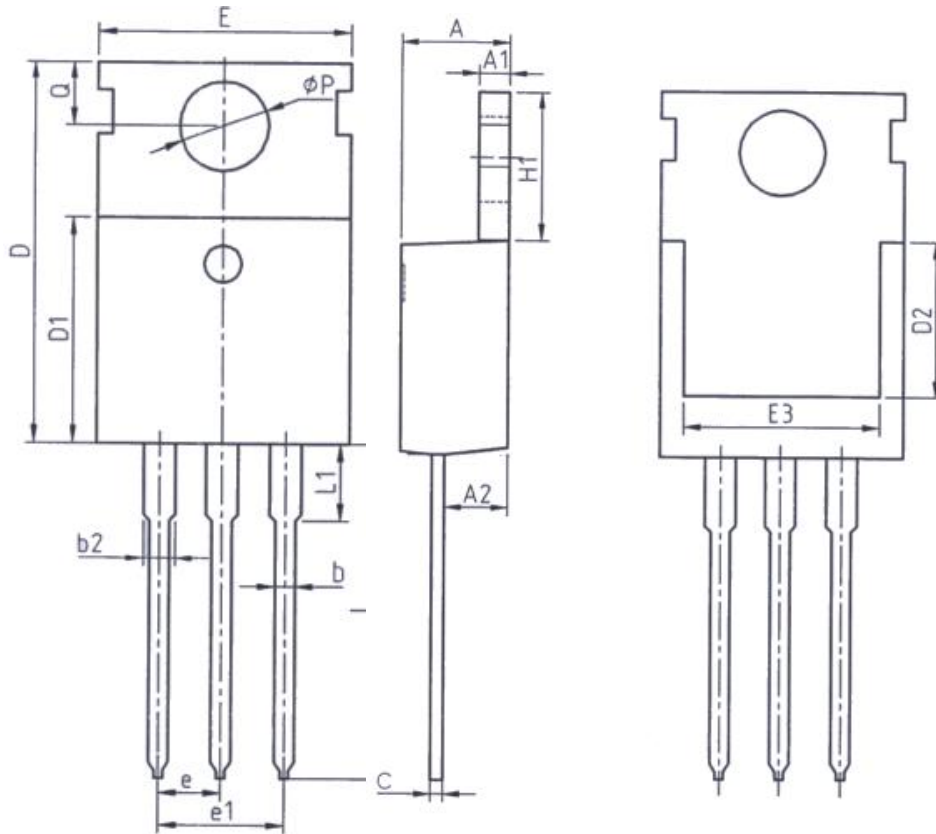


Unit: mm		
Symbol	Min.	Max.
A	2.20	2.40
A1	0.00	0.20
A2	0.97	1.17
b	0.68	0.90
b3	5.20	5.50
c	0.43	0.63
D	5.98	6.22
D1	5.30REF	
E	6.40	6.80
E1	4.63	-

Unit: mm		
Symbol	Min.	Max.
e	2.286BSC	
H	9.40	10.50
L	1.38	1.75
L1	2.90REF	
L2	0.51BSC	
L3	0.88	1.28
L4	-	1.00
L5	1.65	1.95
θ	0°	8°



## TO-220



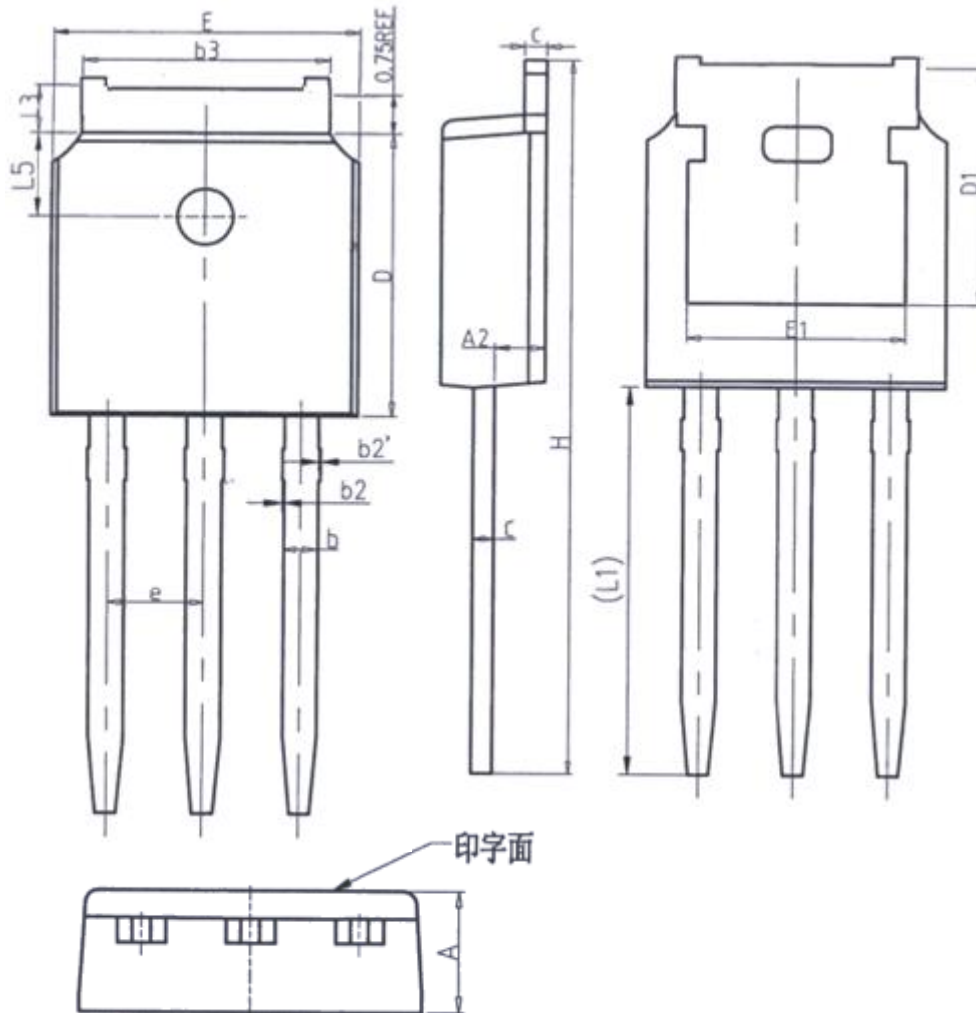
Unit: mm		
Symbol	Min.	Max.
A	4.37	4.77
A1	1.25	1.45
A2	2.20	2.60
b	0.70	0.95
b2	1.17	1.47
c	0.40	0.65
D	15.10	16.10
D1	8.80	9.40
D2	5.50	-

Unit: mm		
Symbol	Min.	Max.
E	9.70	10.30
E3	7.00	-
e	2.54BSC	
e1	5.08BSC	
H1	6.25	6.85
L	12.75	13.80
L1	-	3.40
P	3.40	3.80
Q	2.60	3.00





### TO-251



Unit: mm		
Symbol	Min.	Max.
A	2.20	2.40
A2	0.97	1.17
b	0.68	0.90
b2	0.00	0.10
b2'	0.00	0.10
b3	5.20	5.50
c	0.43	0.63
D	5.98	6.22

Unit: mm		
Symbol	Min.	Max.
D1	5.30REF	
E	6.40	6.80
E1	4.63	-
e	2.286BSC	
H	16.22	16.82
L1	9.15	9.65
L3	0.88	1.28
L5	1.65	1.95



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